



Subject card

Subject name and code	Solid state electronics and nanoelectronics, PG_00037001						
Field of study	Nanotechnology						
Date of commencement of studies	October 2025		Academic year of realisation of subject		2025/2026		
Education level	second-cycle studies		Subject group		Specialty subject group Subject group related to scientific research in the field of study		
Mode of study	Full-time studies		Mode of delivery		at the university		
Year of study	1		Language of instruction		English		
Semester of study	2		ECTS credits		2.0		
Learning profile	general academic profile		Assessment form		exam		
Conducting unit	Department Of Solid State Physics -> Faculty Of Applied Physics And Mathematics -> Wydziały Politechniki Gdańskiej]						
Name and surname of lecturer (lecturers)	Subject supervisor		prof. dr hab. inż. Barbara Kościelska				
	Teachers		prof. dr hab. inż. Barbara Kościelska				
Lesson types and methods of instruction	Lesson type	Lecture	Tutorial	Laboratory	Project	Seminar	SUM
	Number of study hours	30.0	0.0	0.0	0.0	0.0	30
	E-learning hours included: 0.0						
Learning activity and number of study hours	Learning activity	Participation in didactic classes included in study plan		Participation in consultation hours		Self-study	SUM
	Number of study hours	30		2.0		18.0	50
Subject objectives	The aim of the course is to acquire knowledge, skills and competence in the field of solid state electronics and nanoelectronics.						
Learning outcomes	Course outcome		Subject outcome		Method of verification		
	[K7_W02] has enhanced, theoretically supported, detailed knowledge of selected branches of nanotechnology and, according to the needs, within the scope of related fields of science and technology.		Posessing the detailed knowledge of the selected field of nanotechnology and related scientific disciplines		[SW1] Assessment of factual knowledge		
	[K7_K09] is aware of the importance and understands non-technical aspects and results of engineering work, including its influence on the environment, and the related responsibility for decisions made.		Understanding non-technical aspects and effects of engineering activities.		[SK2] Assessment of progress of work		
	[K7_U07] can apply the obtained specialist knowledge to the problems within exact sciences, natural or technical sciences.		Ability to use the obtained knowledge in other fields of science		[SU1] Assessment of task fulfilment		
	[K7_W03] has general knowledge on current development directions and discoveries in physics, chemistry, technology and applications of nanostructures.		Posessing the knowledge of the newest trends and discoveries in the field of nanostructures		[SW1] Assessment of factual knowledge		

Subject contents	<p>1. Introduction.</p> <p>2. Physics and properties of solids - a review</p> <p>2.1. Density of states in 0D, 1D, 2D and 3D materials.</p> <p>2.2. Band structure of solids: free electron, nearly free electron and tight binding model.</p> <p>2.3. Energy bands and carrier concentration in thermal equilibrium.</p> <p>2.4. Electrical and thermal conduction in solids: carrier transport phenomena.</p> <p>2.5. Kinetic phenomena in semiconductors.</p> <p>3. Metal-semiconductor junctions and p-n junctions.</p> <p>4. Diodes: Schottky diode, p-n diode, MIS, MOS, tunnel diode, resonant-tunneling diode.</p> <p>5. Transistors: bipolar, FET, hot-electron HET and THET, single-electron transistor.</p> <p>6. Light emitting diodes and lasers.</p> <p>6.1. Light emitting diodes.</p> <p>6.2. Semiconductor lasers.</p> <p>6.3. Quantum-cascade laser.</p> <p>7. Photodetectors and solar cells.</p> <p>8. Tunnel phenomena in superconductors: Josephson junction.</p> <p>9. Spintronic devices.</p> <p>10. Semiconductor technology.</p> <p>10.1. Crystal growth and epitaxy.</p> <p>10.2. Film formation.</p> <p>10.3. Lithography and etching.</p> <p>10.4. Impurity doping.</p>		
Prerequisites and co-requisites	Completed courses in the field of basics of nanotechnology and solid state physics (or physics of materials).		
Assessment methods and criteria	Subject passing criteria	Passing threshold	Percentage of the final grade
	written test	50.0%	100.0%

Recommended reading	Basic literature	<p>1. S.O. Kasap "Principles of electronic materials and devices", McGraw-Hill, 2006,</p> <p>3rd ed. (EI 178223-00-00/01)</p> <p>2. S.M. Sze, Kwok K. Ng, Physics of Semiconductor Devices, John Wiley & Sons, 2007, 3rd ed. (FM 304796-00-00/01)</p>
	Supplementary literature	<p>1. S.M. Sze, M.K. Lee Semiconductor Devices, Physics and Technology,</p> <p>John Wiley & Sons, 2012, 3rd ed.</p>
	eResources addresses	Adresy na platformie eNauczanie:
Example issues/ example questions/ tasks being completed	<p>Describe metal-semiconductor junction</p> <p>Describe MOS diode</p> <p>Describe single electron transistor</p> <p>Describe quantum-cascade laser</p>	
Work placement	Not applicable	

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